Surface Mount Schottky Power Rectifier

POWERMITE® Power Surface Mount Package

The Schottky Powermite employs the Schottky Barrier principle with a barrier metal and epitaxial construction that produces optimal forward voltage drop-reverse current tradeoff. The advanced packaging techniques provide for a highly efficient micro miniature, space saving surface mount Rectifier. With its unique heatsink design, the Powermite has the same thermal performance as the SMA while being 50% smaller in footprint area, and delivering one of the lowest height profiles, < 1.1 mm in the industry. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are ac/dc and dc-dc converters, reverse battery protection, and "Oring" of multiple supply voltages and any other application where performance and size are critical.

Features:

- Low Profile Maximum Height of 1.1 mm
- Small Footprint Footprint Area of 8.45 mm2
- Low V_F Provides Higher Efficiency and Extends Battery Life
- Supplied in 12 mm Tape and Reel
- Low Thermal Resistance with Direct Thermal Path of Die on Exposed Cathode Heat Sink

Mechanical Characteristics:

- Powermite is JEDEC Registered as DO-216AA
- Case: Molded Epoxy
- Epoxy Meets UL94V-0 at 1/8"
- Weight: 62 mg (approximately)
- Device Marking: BCJ
- Lead and Mounting Surface Temperature for Soldering Purposes.
 260°C Maximum for 10 Seconds

MAXIMUM RATINGS

Please See the Table on the Following Page



ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES 40 VOLTS



POWERMITE CASE 457 PLASTIC

MARKING DIAGRAM



BCJ = Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping
MBRM140T1	POWERMITE	3000/Tape & Reel
MBRM140T3	POWERMITE	12,000/Tape & Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	40	V
Average Rectified Forward Current (At Rated V _R , T _C = 110°C)	I _O	1.0	А
Peak Repetitive Forward Current (At Rated V _R , Square Wave, 100 kHz, T _C = 110°C)	IFRM	2.0	А
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	I _{FSM}	50	А
Storage Temperature	T _{stg}	-55 to 150	°C
Operating Junction Temperature	TJ	-55 to 125	°C
Voltage Rate of Change (Rated V _R , T _J = 25°C)	dv/dt	10,000	V/μs

THERMAL CHARACTERISTICS

Thermal Resistance - Junction-to-Lead (Anode) (Note 1)	R _{til}	35	°C/W	
Thermal Resistance - Junction-to-Tab (Cathode) (Note 1)	R _{titab}	23		ĺ
Thermal Resistance - Junction-to-Ambient (Note 1)	Ř _{tja}	277		ĺ

^{1.} Mounted with minimum recommended pad size, PC Board FR4, See Figures 9 & 10.

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 2), See Figure 2	V _F	T _J = 25°C	T _J = 85°C	V
(I _F = 0.1 A) (I _F = 1.0 A) (I _F = 3.0 A)		0.36 0.55 0.85	0.30 0.515 0.88	
Maximum Instantaneous Reverse Current (Note 2), See Figure 4	I _R	T _J = 25°C	T _J = 85°C	mA
$(V_R = 40 \text{ V})$ $(V_R = 20 \text{ V})$		0.5 0.15	25 18	

^{2.} Pulse Test: Pulse Width \leq 250 μ s, Duty Cycle \leq 2%.

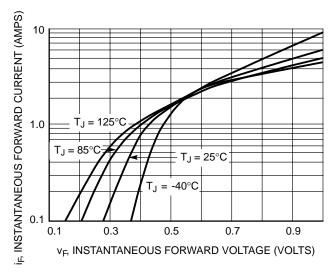


Figure 1. Typical Forward Voltage

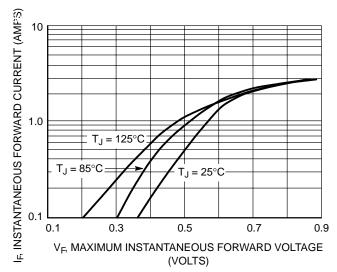


Figure 2. Maximum Forward Voltage

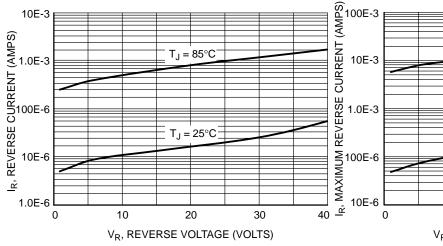


Figure 3. Typical Reverse Current

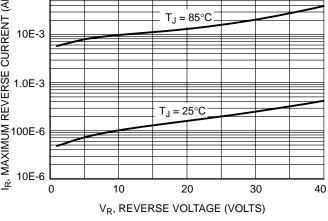
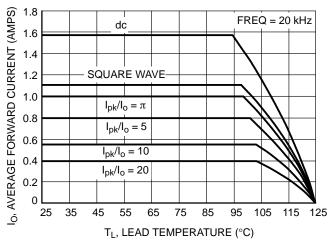


Figure 4. Maximum Reverse Current



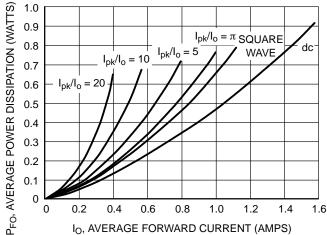
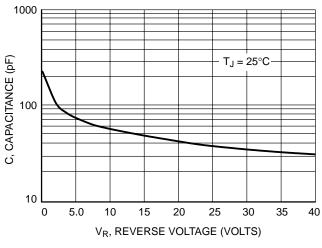


Figure 5. Current Derating

Figure 6. Forward Power Dissipation



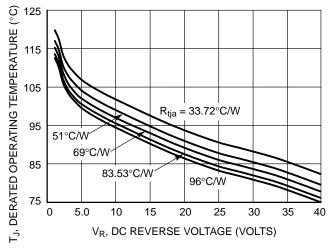


Figure 7. Capacitance

Figure 8. Typical Operating Temperature Derating*

r(t) = thermal impedance under given conditions,

Pf = forward power dissipation, and

Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

^{*} Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where

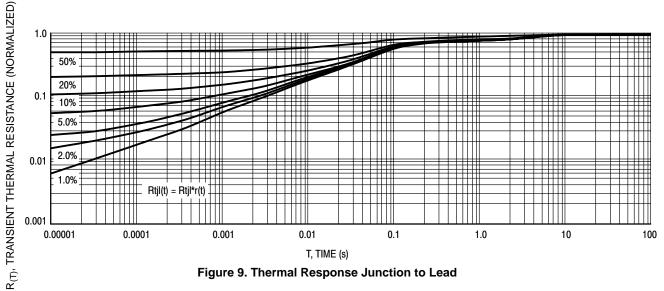


Figure 9. Thermal Response Junction to Lead

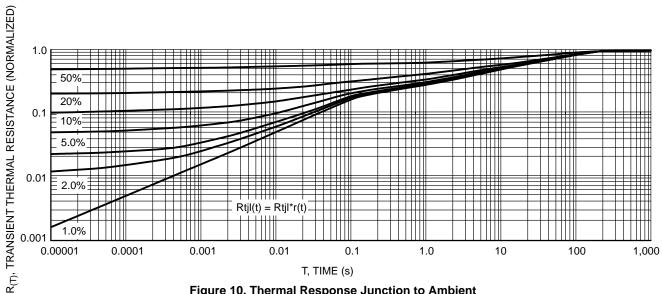
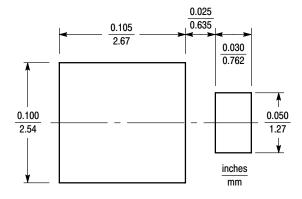


Figure 10. Thermal Response Junction to Ambient

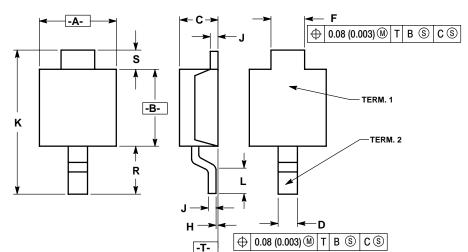


Minimum Recommended Footprint

PACKAGE DIMENSIONS

POWERMITE

PLASTIC PACKAGE CASE 457-04 ISSUE D



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH,

 MIN	MAX	MIN	MAX	1
MILLIMETERS		INCHES		
			SHALL N	ОТ
PROT PROT	PROTRUSIONS PROTRUSIONS EXCEED 0.15 (I	PROTRUSIONS OR GAT PROTRUSIONS OR GAT EXCEED 0.15 (0.006) PE	PROTRUSIONS OR GATE BURRS PROTRUSIONS OR GATE BURRS EXCEED 0.15 (0.006) PER SIDE. MILLIMETERS INC	MILLIMETERS INCHES

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.75	2.05	0.069	0.081
В	1.75	2.18	0.069	0.086
С	0.85	1.15	0.033	0.045
D	0.40	0.69	0.016	0.027
F	0.70	1.00	0.028	0.039
Н	-0.05	+0.10	-0.002	+0.004
J	0.10	0.25	0.004	0.010
K	3.60	3.90	0.142	0.154
L	0.50	0.80	0.020	0.031
R	1.20	1.50	0.047	0.059
S	0.50 REF		0.019 REF	

Notes

POWERMITE is a registered trademark of and used under a license from MicroSemi Corporation.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada **Fax**: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051

Phone: 81-3-5773-3850 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local

Sales Representative.